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Team Nexperia

HEF4555B-Q100

1-of-4 decoder/demultiplexer

Rev. 1 — 21 October 2013

Product data sheet

1. General description

The HEF4555B-Q100 contains two 1-of-4 decoders/demultiplexers. Each decoder/demultiplexer has two address inputs, nA0 and nA1. They also have an active LOW enable input ($n\bar{E}$) and four mutually exclusive outputs which are active HIGH (nY_0 to nY_3). When used as a decoder, $n\bar{E}$ when HIGH, forces nY_0 to nY_3 LOW. When used as a demultiplexer, the information on nA0 and nA1 with $n\bar{E}$ as data input selects the appropriate output. All unselected outputs are LOW.

It operates over a recommended V_{DD} power supply range of 3 V to 15 V referenced to V_{SS} (usually ground). Unused inputs must be connected to V_{DD} , V_{SS} , or another input.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 3) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 3)
 - ◆ Specified from -40 °C to +85 °C
- Fully static operation
- 5 V, 10 V, and 15 V parametric ratings
- Standardized symmetrical output characteristics
- ESD protection:
 - ◆ MIL-STD-883, method 3015 exceeds 2000 V
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V ($C = 200 \text{ pF}$, $R = 0 \Omega$)
- Complies with JEDEC standard JESD 13-B

3. Applications

- Code conversion
- Address decoding
- Demultiplexing: when using the enable input as data input



4. Ordering information

Table 1. Ordering information

All types operate from -40°C to $+85^{\circ}\text{C}$.

Type number	Package		Version
	Name	Description	
HEF4555BT-Q100	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1

5. Functional diagram

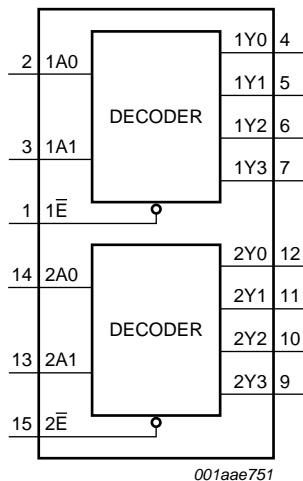


Fig 1. Functional diagram

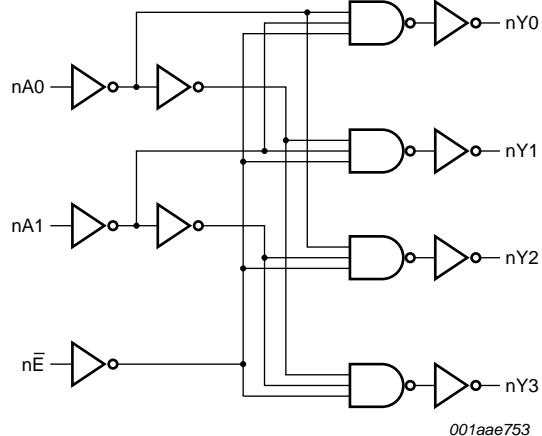


Fig 2. Logic diagram for one decoder/multiplexer

6. Pinning information

6.1 Pinning

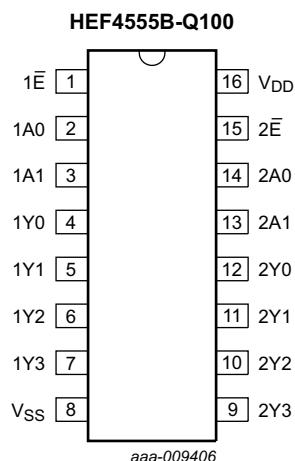


Fig 3. Pin configuration

6.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1A0, 1A1, 2A0, 2A1	2, 3, 14, 13	address input
1̄E, 2̄E	1, 15	enable input (active LOW)
1Y0, 1Y1, 1Y2, 1Y3, 2Y0, 2Y1, 2Y2, 2Y3	4, 5, 6, 7, 12, 11, 10, 9	output (active HIGH)
V _{DD}	16	supply voltage
V _{SS}	8	ground (GND)

7. Functional description

Table 3. Function selection^[1]

Inputs			Outputs			
n̄E	nA0	nA1	nY0	nY1	nY2	nY3
L	L	L	H	L	L	L
L	H	L	L	H	L	L
L	L	H	L	L	H	L
L	H	H	L	L	L	H
H	X	X	L	L	L	L

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care.

8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
V _{DD}	supply voltage		-0.5	+18	V	
I _{IK}	input clamping current	V _I < -0.5 V or V _I > V _{DD} + 0.5 V	-	±10	mA	
V _I	input voltage		-0.5	V _{DD} + 0.5	V	
I _{OK}	output clamping current	V _O < -0.5 V or V _O > V _{DD} + 0.5 V	-	±10	mA	
I _{I/O}	input/output current		-	±10	mA	
I _{DD}	supply current		-	50	mA	
T _{stg}	storage temperature		-65	+150	°C	
T _{amb}	ambient temperature		-40	+85	°C	
P _{tot}	total power dissipation	T _{amb} -40 °C to +85 °C	[1]	-	500	mW
P	power dissipation	per output	-	100	mW	

[1] For SO16 package: P_{tot} derates linearly with 8 mW/K above 70 °C.

9. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DD}	supply voltage		3	-	15	V
V_I	input voltage		0	-	V_{DD}	V
T_{amb}	ambient temperature	in free air	-40	-	+85	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{DD} = 5\text{ V}$	-	-	3.75	$\mu\text{s}/\text{V}$
		$V_{DD} = 10\text{ V}$	-	-	0.5	$\mu\text{s}/\text{V}$
		$V_{DD} = 15\text{ V}$	-	-	0.08	$\mu\text{s}/\text{V}$

10. Static characteristics

Table 6. Static characteristics

$V_{SS} = 0\text{ V}$; $V_I = V_{SS}$ or V_{DD} unless otherwise specified.

Symbol	Parameter	Conditions	V_{DD}	$T_{amb} = -40\text{ °C}$		$T_{amb} = 25\text{ °C}$		$T_{amb} = 85\text{ °C}$		Unit
				Min	Max	Min	Max	Min	Max	
V_{IH}	HIGH-level input voltage $ I_O < 1\text{ }\mu\text{A}$		5 V	3.5	-	3.5	-	3.5	-	V
			10 V	7.0	-	7.0	-	7.0	-	V
			15 V	11.0	-	11.0	-	11.0	-	V
V_{IL}	LOW-level input voltage $ I_O < 1\text{ }\mu\text{A}$		5 V	-	1.5	-	1.5	-	1.5	V
			10 V	-	3.0	-	3.0	-	3.0	V
			15 V	-	4.0	-	4.0	-	4.0	V
V_{OH}	HIGH-level output voltage $V_I = V_{SS}$ or V_{DD} $ I_O < 1\text{ }\mu\text{A}$		5 V	4.95	-	4.95	-	4.95	-	V
			10 V	9.95	-	9.95	-	9.95	-	V
			15 V	14.95	-	14.95	-	14.95	-	V
V_{OL}	LOW-level output voltage $V_I = V_{SS}$ or V_{DD} $ I_O < 1\text{ }\mu\text{A}$		5 V	-	0.05	-	0.05	-	0.05	V
			10 V	-	0.05	-	0.05	-	0.05	V
			15 V	-	0.05	-	0.05	-	0.05	V
I_{OH}	HIGH-level output current $V_O = 2.5\text{ V}$ $V_O = 4.6\text{ V}$ $V_O = 9.5\text{ V}$ $V_O = 13.5\text{ V}$		5 V	-	-1.7	-	-1.4	-	-1.1	mA
			5 V	-	-0.52	-	-0.44	-	-0.36	mA
			10 V	-	-1.3	-	-1.1	-	-0.9	mA
			15 V	-	-3.6	-	-3.0	-	-2.4	mA
I_{OL}	LOW-level output current $V_O = 0.4\text{ V}$ $V_O = 0.5\text{ V}$ $V_O = 1.5\text{ V}$		5 V	0.52	-	0.44	-	0.36	-	mA
			10 V	1.3	-	1.1	-	0.9	-	mA
			15 V	3.6	-	3.0	-	2.4	-	mA
I_I	input leakage current	$V_{DD} = 15\text{ V}$	15 V	-	± 0.3	-	± 0.3	-	± 1.0	μA
I_{DD}	supply current $I_O = 0\text{ A}$ $V_I = V_{SS}$ or V_{DD}		5 V	-	20	-	20	-	150	μA
			10 V	-	40	-	40	-	300	μA
			15 V	-	80	-	80	-	600	μA
C_I	input capacitance		-	-	-	-	7.5	-	-	pF

11. Dynamic characteristics

Table 7. Dynamic characteristics

$V_{SS} = 0 \text{ V}$; $T_{amb} = 25 \text{ }^{\circ}\text{C}$; for test circuit, see [Figure 5](#); unless otherwise specified.

Symbol	Parameter	Conditions	V_{DD}	Extrapolation formula	Min	Typ	Max	Unit	
t_{PHL}	HIGH to LOW propagation delay nAn → nYn; see Figure 4	nAn → nYn	5 V	[1]	88 ns + (0.55 ns/pF) C_L	-	115	230	ns
			10 V		34 ns + (0.23 ns/pF) C_L	-	45	90	ns
			15 V		22 ns + (0.16 ns/pF) C_L	-	30	65	ns
		$n\bar{E} \rightarrow nYn$	5 V		98 ns + (0.55 ns/pF) C_L	-	125	250	ns
			10 V		39 ns + (0.23 ns/pF) C_L	-	50	95	ns
			15 V		22 ns + (0.16 ns/pF) C_L	-	30	65	ns
t_{PLH}	LOW to HIGH propagation delay nAn → nYn	nAn → nYn	5 V	[1]	113 ns + (0.55 ns/pF) C_L	-	140	280	ns
			10 V		44 ns + (0.23 ns/pF) C_L	-	55	105	ns
			15 V		32 ns + (0.16 ns/pF) C_L	-	40	75	ns
		$n\bar{E} \rightarrow nYn$	5 V		123 ns + (0.55 ns/pF) C_L	-	150	295	ns
			10 V		44 ns + (0.23 ns/pF) C_L	-	55	110	ns
			15 V		32 ns + (0.16 ns/pF) C_L	-	40	75	ns
t_t	transition time	on nYn	5 V	[1][2]	10 ns + (1.00 ns/pF) C_L	-	60	120	ns
			10 V		9 ns + (0.42 ns/pF) C_L	-	30	60	ns
			15 V		6 ns + (0.28 ns/pF) C_L	-	20	40	ns

[1] The typical values of the propagation delay and transition times are calculated from the extrapolation formulas shown (C_L in pF).

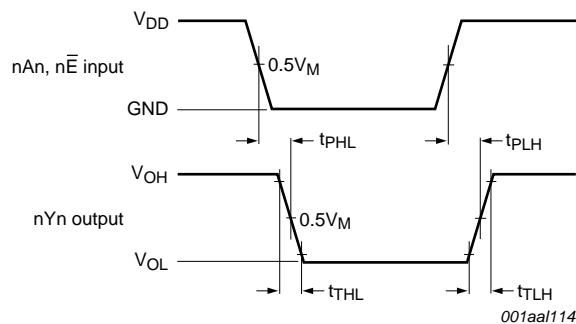
[2] Transition time t_t is the same as the HIGH to LOW and LOW to HIGH transition times t_{THL} and t_{TLH} .

Table 8. Dynamic power dissipation P_D

P_D can be calculated from the formulas shown. $V_{SS} = 0 \text{ V}$; $t_i = t_f \leq 20 \text{ ns}$; $T_{amb} = 25 \text{ }^{\circ}\text{C}$.

Symbol	Parameter	V_{DD}	Typical formula for P_D (μW)	Where:
P_D	dynamic power dissipation	5 V	$P_D = 4500 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2$	f_i = input frequency in MHz,
		10 V	$P_D = 18800 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2$	f_o = output frequency in MHz,
		15 V	$P_D = 45700 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2$	C_L = output load capacitance in pF, V_{DD} = supply voltage in V, $\Sigma(f_o \times C_L)$ = sum of the outputs.

12. Waveforms



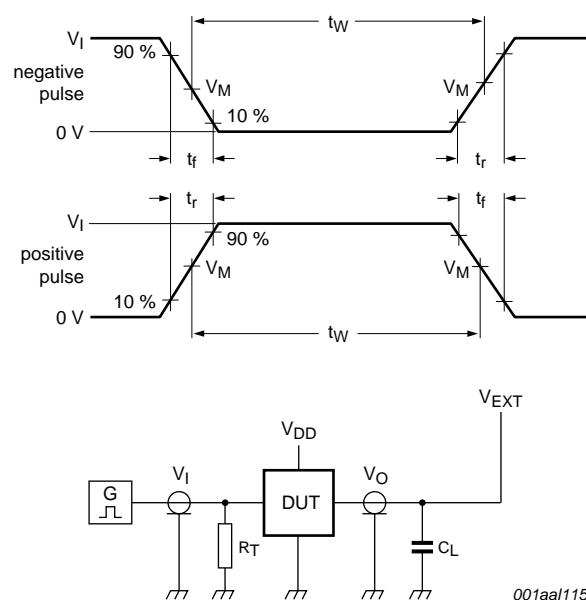
Measurement points are given in [Table 9](#).

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 4. Inputs nAn and $n\bar{E}$ to output nYn propagation delays

Table 9. Measurement points

Supply voltage	Input	Output
V_{DD} 5 V to 15 V	V_M $0.5V_{DD}$	V_M $0.5V_{DD}$



Test data is given in [Table 10](#).

Definitions for test circuit:

Device Under Test (DUT);

R_L = Load resistance;

C_L = Load capacitance including jig and probe capacitance;

R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator;

V_{EXT} = External voltage for measuring switching times.

Fig 5. Load circuitry for switching times

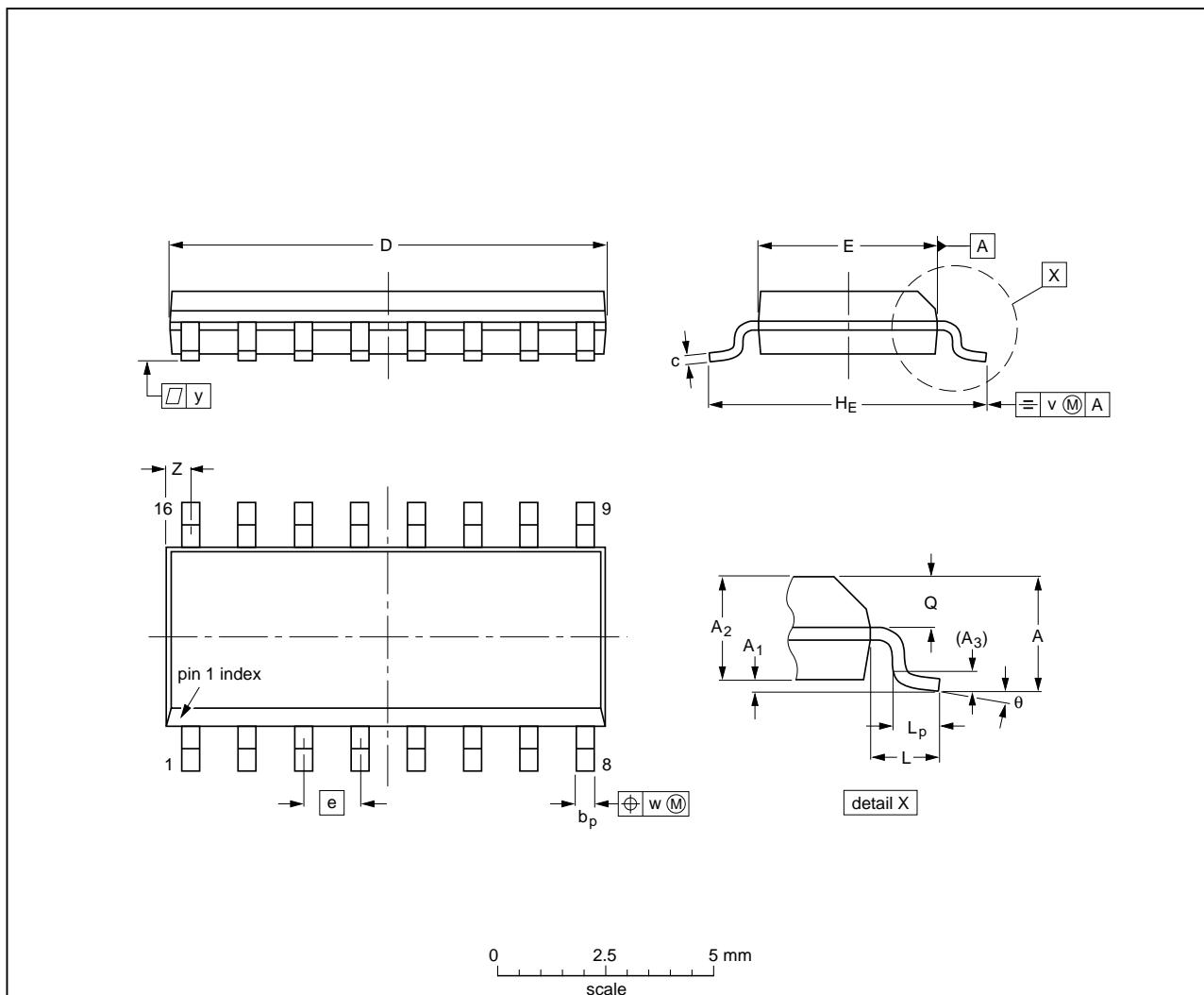
Table 10. Test data

Supply voltage	Input		C_L	t_{PLH}, t_{PHL}	t_{THL}, t_{TLH}
	V_I	$t_r = t_f$			
5 V to 15 V	V_{DD}	$\leq 20 \text{ ns}$	50 pF	open	V_{DD}

13. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽¹⁾	e	H _E	L	L _p	Q	v	w	y	Z ⁽¹⁾	θ
mm	1.75 0.10	0.25 0.125	1.45 1.25	0.25	0.49 0.36	0.25 0.19	10.0 9.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8° 0°
inches	0.069 0.004	0.010 0.049	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.39 0.38	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.020	0.01	0.01	0.004	0.028 0.012	

Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT109-1	076E07	MS-012				99-12-27 03-02-19

Fig 6. Package outline SOT109-1 (SO16)

14. Abbreviations

Table 11. Abbreviations

Acronym	Description
HBM	Human Body Model
ESD	ElectroStatic Discharge
MM	Machine Model
MIL	Military

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
HEF4555B_Q100 v.1	20131021	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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